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## Hexaiododisilane

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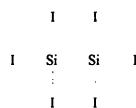
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### Abstract

The title compound,  $\text{Si}_2\text{I}_6$ , was prepared by the reaction of silicon tetraiodide with finely divided metallic silver and was subsequently purified by sublimation. The crystal structure can be regarded as an approximately dense packing of I atoms with the sequence ABAC with Si–Si dumb-bells occupying one-sixth of the octahedral sites. In an alternative description, the structure is composed of hexaiododisilane molecules with staggered conformation forming isolated, slightly distorted octahedra with Si–Si dumb-bells in the centres.

### Comment

During the course of our investigations of silicon suboxides, the title compound was found to be a potential precursor for the preparation of silicon sesquioxide (Suresh & Padma, 1984; Belot *et al.*, 1991). The crystal structure of hexaiododisilane is the first of a hexahalogendisilane to be reported.



The hexaiododisilane molecules are arranged in a staggered conformation in which each Si atom is surrounded tetrahedrally by three I atoms and another Si atom. The I atoms form an ABAC layer structure where one-sixth of the octahedral sites are occupied by Si–Si dumb-bells. The site symmetry of hexaiododisilane is  $C_s$  and within the limits of experimental error the point-group symmetry is  $D_{3d}$ . The Si–I bond lengths

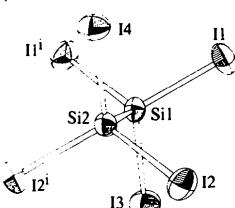


Fig. 1. A view of the staggered conformation of hexaiododisilane. Displacement ellipsoids are shown at the 50% probability level. [Symmetry code: (i)  $x, \frac{1}{2} - y, z$ .]

in the title compound are in good agreement with the bond length reported for silicon tetraiodide (Hassel & Kringstad, 1931). The Si–Si bond length is in the same range as those of the analogous disilanes  $\text{Si}_2\text{H}_6$  (Beagley *et al.*, 1972) and  $\text{Si}_2\text{F}_6$  (Oberhammer, 1976), which were determined by gas-phase electron diffraction.

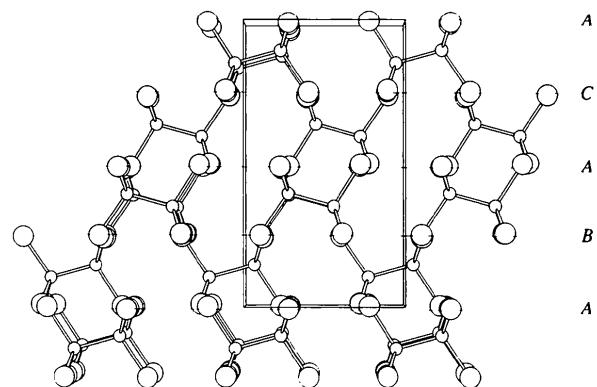


Fig. 2. Packing of I atoms with the sequence ABAC and Si–Si dumb-bells in one-sixth of the octahedral sites. Large circles are I atoms, small circles are Si atoms.

### Experimental

Hexaiododisilane was prepared by a standard method (Friedel & Ladenburg, 1869; Schwarz & Pflugmacher, 1942; Peteriet, 1964) in which silicon tetraiodide was reacted with finely divided metallic silver in an evacuated glass tube at 673 K for 3 h. Subsequent sublimation yields hexaiododisilane as colourless needles.

### Crystal data

$\text{Si}_2\text{I}_6$	Mo $K\alpha$ radiation
$M_r = 817.58$	$\lambda = 0.71073 \text{ \AA}$
Orthorhombic	Cell parameters from 21 reflections
$Pnma$	$\theta = 0 \rightarrow 30^\circ$
$a = 13.702 (2) \text{ \AA}$	$\mu = 13.907 \text{ mm}^{-1}$
$b = 12.498 (2) \text{ \AA}$	$T = 293 (2) \text{ K}$
$c = 7.8940 (10) \text{ \AA}$	Needle
$V = 1351.8 (4) \text{ \AA}^3$	$1 \times 0.3 \times 0.1 \text{ mm}$
$Z = 4$	Colourless
$D_x = 4.017 \text{ Mg m}^{-3}$	

### Data collection

Enraf–Nonius CAD-4 diffractometer	$R_{\text{int}} = 0.0290$
Variable $\omega/2\theta$ scans	$\theta_{\text{max}} = 30.01^\circ$
Absorption correction:	$h = 0 \rightarrow 19$
numerical ( <i>SHELX76</i> ; Sheldrick, 1976)	$k = 0 \rightarrow 17$
$T_{\text{min}} = 0.0249$ , $T_{\text{max}} = 0.0754$	$l = 0 \rightarrow 11$
3665 measured reflections	3 standard reflections frequency: 60 min
1964 independent reflections	intensity decay: none

*Refinement*

Refinement on  $F^2$   
 $R[F^2 > 2\sigma(F^2)] = 0.0608$   
 $wR(F^2) = 0.1650$   
 $S = 1.306$   
1964 reflections  
44 parameters  
 $w = 1/[\sigma^2(F_o^2) + (0.0765P)^2 + 10.7170P]$   
where  $P = (F_o^2 + 2F_c^2)/3$   
 $(\Delta/\sigma)_{\max} < 0.001$   
 $\Delta\rho_{\max} = 1.75 \text{ e } \text{\AA}^{-3}$   
 $\Delta\rho_{\min} = -2.23 \text{ e } \text{\AA}^{-3}$

Extinction correction:  
*SHELXL93* (Sheldrick, 1993; Larson, 1970)  
Extinction coefficient:  
0.0019 (2)  
Atomic scattering factors  
from *International Tables for Crystallography* (1992,  
Vol. C, Tables 4.2.6.8 and  
6.1.1.4)

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Table 1. Fractional atomic coordinates and equivalent isotropic displacement parameters ( $\text{\AA}^2$ )

$$U_{eq} = (1/3)\sum_i \sum_j U_{ij} a_i^* a_j^* \mathbf{a}_i \cdot \mathbf{a}_j.$$

	$x$	$y$	$z$	$U_{eq}$
I1	0.24321 (5)	0.41001 (5)	0.11088 (10)	0.0560 (3)
I2	0.00717 (5)	0.41080 (5)	-0.27616 (10)	0.0565 (3)
I3	-0.00093 (6)	1/4	0.22388 (13)	0.0553 (3)
I4	0.24813 (6)	1/4	-0.39933 (12)	0.0539 (3)
Si1	0.1479 (2)	1/4	0.0569 (4)	0.0349 (6)
Si2	0.1019 (2)	1/4	-0.2264 (4)	0.0339 (6)

Table 2. Selected geometric parameters ( $\text{\AA}$ , °)

Si1—I1	2.427 (2)	Si1—Si2	2.323 (4)
Si2—I2	2.425 (2)	Si1—I1'	2.427 (2)
Si1—I3	2.428 (3)	Si2—I2'	2.424 (2)
Si2—I4	2.424 (3)		
Si2—Si1—I1'	108.37 (10)	Si1—Si2—I4	108.5 (2)
Si2—Si1—I1	108.37 (10)	Si1—Si2—I2'	107.50 (10)
I1'—Si1—I1	111.01 (13)	I4—Si2—I2'	110.57 (9)
Si2—Si1—I3	107.2 (2)	Si1—Si2—I2	107.50 (10)
I1'—Si1—I3	110.88 (9)	I4—Si2—I2	110.57 (9)
I1—Si1—I3	110.88 (9)	I2'—Si2—I2	112.00 (13)

Symmetry code: (i)  $x, \frac{1}{2} - y, z$ .

Data collection: *CAD-4 Software* (Enraf–Nonius, 1989). Cell refinement: *CAD-4 Software CELDIM*. Data reduction: *CAD-4 Software CADSHELL*. Program(s) used to solve structure: *SHELXS86* (Sheldrick, 1985). Program(s) used to refine structure: *SHELXL93* (Sheldrick, 1993). Molecular graphics: *ORTEPII* (Johnson, 1971). Software used to prepare material for publication: *SHELXL93*.

Lists of structure factors, anisotropic displacement parameters and complete geometry have been deposited with the IUCr (Reference: BR1117). Copies may be obtained through The Managing Editor, International Union of Crystallography, 5 Abbey Square, Chester CH1 2HU, England.

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## K<sub>2</sub>MoO<sub>2</sub>As<sub>2</sub>O<sub>7</sub>

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## Abstract

The dipotassium molybdyl diarsenate(4-) structure is built up from MoO<sub>6</sub> octahedra and As<sub>2</sub>O<sub>7</sub> groups sharing corners to form layers. The two O atoms of the molybdyl group remain unshared with short Mo—O distances (average 1.704 Å). The K<sup>+</sup> ions are located in the interlayer space. A relationship is found between the two-dimensional structure of the title compound and the three-dimensional melilite structure.

## Commentaire

Dans le cadre de la recherche de nouveaux matériaux, à structure ouverte, nous avons précédemment explorés les systèmes *A*—M—As—O (*A* = alcalin, *M* = Nb, V, Al et Mo). Plusieurs composés ont été caractérisés et étudiés: K<sub>2</sub>Nb<sub>2</sub>As<sub>2</sub>O<sub>11</sub> (Zid, Jouini, Jouini & Omezzine, 1988), K<sub>3</sub>NbAs<sub>2</sub>O<sub>9</sub> (Zid, Jouini, Jouini & Omezzine, 1989), KNb<sub>4</sub>AsO<sub>13</sub> (Haddad, Jouini, Jouini & Piffard, 1988), NaVOAsO<sub>4</sub> (Haddad, Jouini & Piffard, 1992), RbAlAs<sub>2</sub>O<sub>7</sub> (Boughzala, Driss & Jouini, 1993), NaAlAs<sub>2</sub>O<sub>7</sub> (Driss & Jouini, 1994) et KM<sub>2</sub>O<sub>2</sub>AsO<sub>4</sub> (Zid & Jouini, 1995).

La comparaison de la structure de K<sub>2</sub>MoO<sub>2</sub>As<sub>2</sub>O<sub>7</sub> avec celles de composés décrits antérieurement montre que ceux de formulation analogue connus (NH<sub>4</sub>)<sub>2</sub>MoO<sub>2</sub>—P<sub>2</sub>O<sub>7</sub> (Averbuch-Pouchot, 1988) et CsHM<sub>2</sub>O<sub>2</sub>P<sub>2</sub>O<sub>7</sub> (Averbuch-Pouchot, 1989) ont la dimensionnalité 1.